Product Summary

	Value	Unit
	100	V
	3.0	V
	159	A
	3.1	m

	Package	# of Pins	Marking	MSL	T_J (°C)	Media	Quantity (pcs)
	PDFN5x6-8L	8	SH1003N/Lang (x-none)>BDC q 73.2 23.16G.7g			(x-none)>BDC q 73.2 23	

	Symbol		Min.	Typ.	Max.	Unit
	$V_{(BR)DSS}$		100			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1.0	A
		T_J = 55°C			5.0	
Gate-Body Leakage Current	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 A	2.0	3.0	4.0	V
	$R_{DS(ON)}$			3.1	3.7	m
	g_{FS}			37		S
	V_{SD}			0.66	1.0	V
Diode Continuous Current	I_S				159	A
	C_{iss}			6172		pF
	C_{oss}			854		pF
	C_{rss}			17		pF
	R_g			2.5		
	Q_g			89		nC
	Q_g			56		nC
	Q_{gs}			30		nC
	Q_{gd}			17		nC
	$t_{D(on)}$			25		ns
	t_r			34		ns
	$t_{D(off)}$			59		ns
	t_f			27		ns
Body Diode Reverse Recovery Time	t_{rr}	I_F = 20A, dI_F/dt = 100A/ s		108		ns
	Q_{rr}			138		nC

Symbol		Unit
R_{JA}		°C/W
R_{JC}		°C/W

Notes:

Typical Electrical & Thermal Characteristics

Typical Electrical & Thermal Characteristics

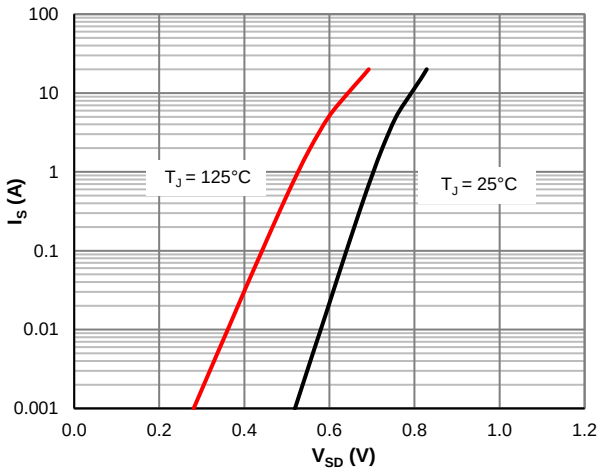


Figure 7: Body-Diode Characteristics

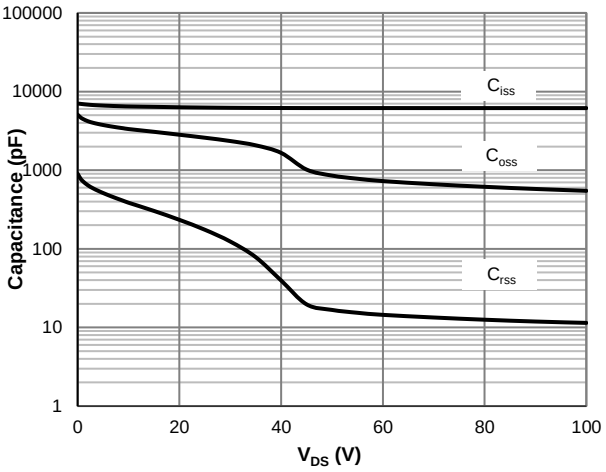


Figure 8: Capacitance Characteristics

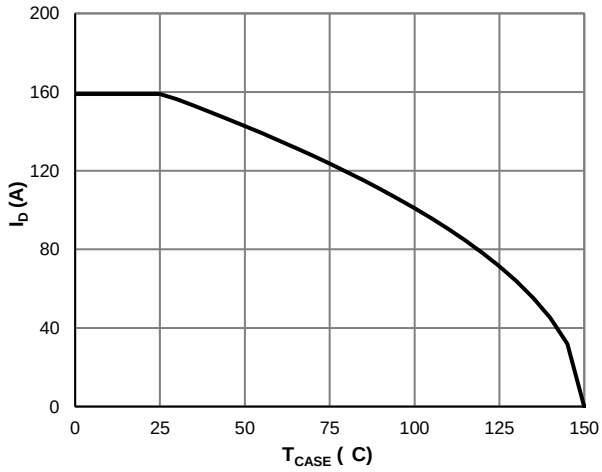


Figure 9: Current De-rating

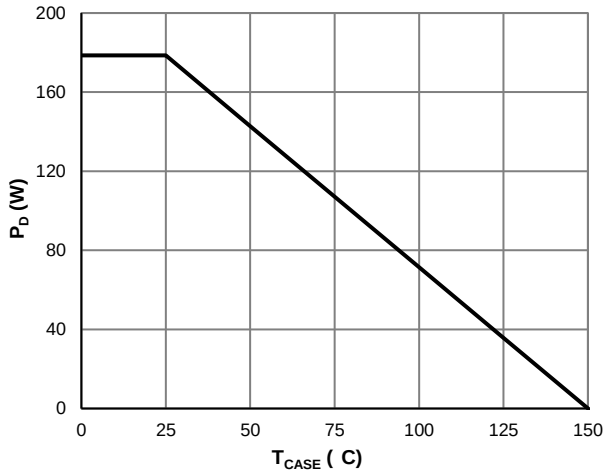


Figure 10: Power De-rating

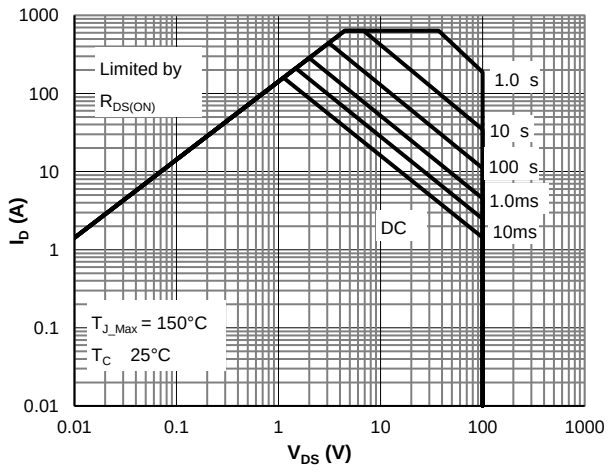


Figure 11: Maximum Safe Operating Area

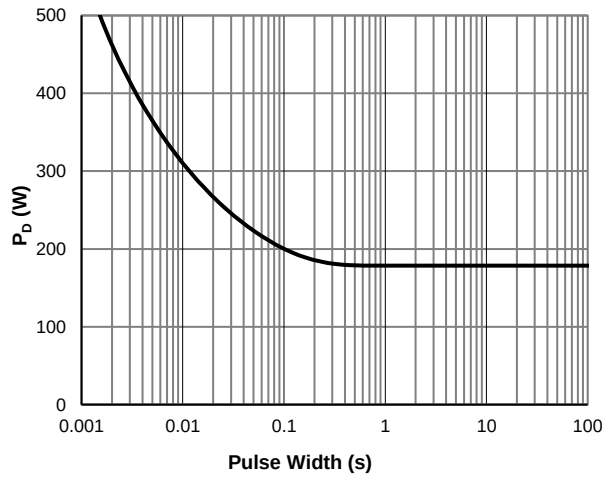
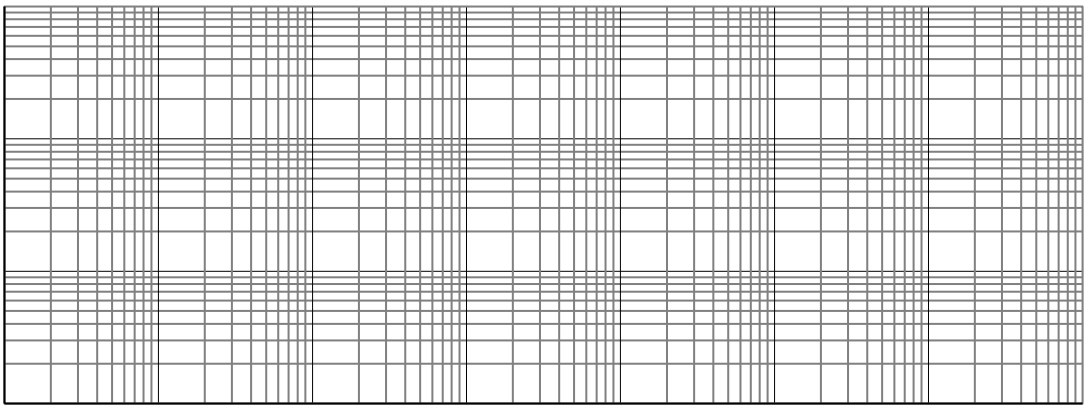


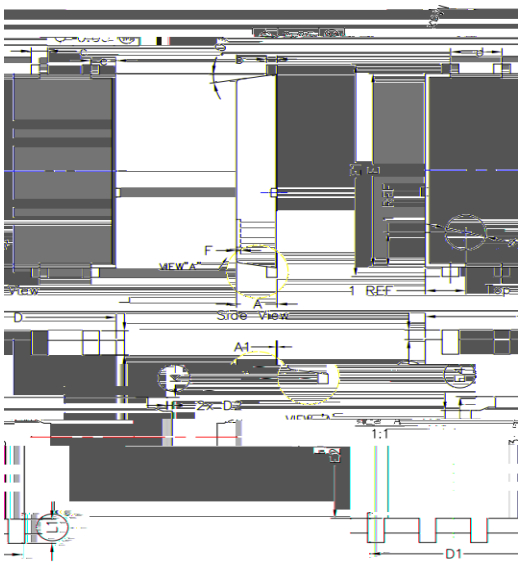
Figure 12: Single Pulse Power Rating, Junction-to-Case

Jiangsu JieJie Microelectronics Co., Ltd.
All product information are copyrighted and subject to legal disclaimers

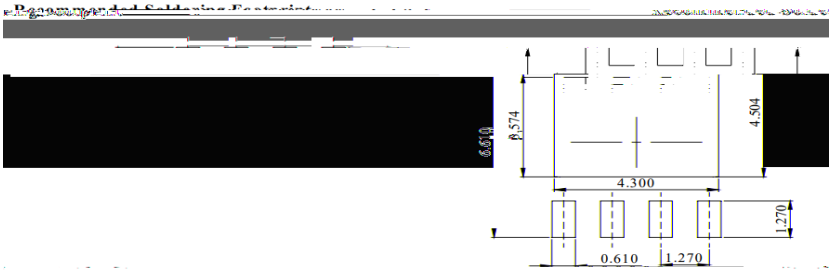
Typical Electrical & Thermal Characteristics



PDFN5x6-8L Package Information







ISIONS:MILLIMETERS DIMEN

Jiangsu JieJie Microelectronics Co., Ltd.
All product information are copyrighted and subject to legal disclaimers